General Purpose Transistor NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	40	Vdc
Collector – Base Voltage	V _{CBO}	75	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ι _C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board $T_A = 25^{\circ}C$	PD	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

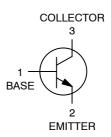


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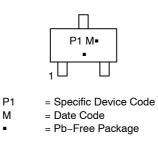
http://onsemi.com



CASE 419 STYLE 3



MARKING DIAGRAM



(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2222AWT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
SMMBT2222AWT1G	SC–70 (Pb–Free)	3,000 / Tape & Reel

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Charact	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (No. $(I_{C} = 1.0 \text{ mAdc}, I_{B} = 0)$	V _{(BR)CEO}	40	-	Vdc	
Collector – Base Breakdown Voltage $(I_C = 10 \ \mu Adc, I_E = 0)$	V _{(BR)CBO}	75	-	Vdc	
Emitter – Base Breakdown Voltage $(I_E = 10 \ \mu Adc, I_C = 0)$	V _{(BR)EBO}	6.0	-	Vdc	
Base Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{BL}	_	20	nAdc	
Collector Cutoff Current (V _{CE} = 60 Vdc, V _{EB} = 3.0 Vdc)	I _{CEX}	_	10	nAdc	
ON CHARACTERISTICS (Note 1)					
$ \begin{array}{l} \text{DC Current Gain (Note 1)} \\ (I_{C} = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \end{array} $	H _{FE}	35 50 75 100 40	- - 300 -	-	
Collector – Emitter Saturation Voltage (Not ($I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$) ($I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$)	V _{CE(sat)}	-	0.3 1.0	Vdc	
Base – Emitter Saturation Voltage (Note 1) (I _C = 150 mAdc, I _B = 15 mAdc) (I _C = 500 mAdc, I _B = 50 mAdc)	V _{BE(sat)}	0.6	1.2 2.0	Vdc	
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 20 mAdc, V _{CE} = 20 Vdc, f = 100 M	lHz)	f _T	300	-	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 1.0 MHz)		C _{obo}	_	8.0	pF
Input Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	30	pF
Input Impedance (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kH	łz)	h _{ie}	0.25	1.25	kΩ
Voltage Feedback Ratio (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kH	h _{re}	-	4.0	X 10 ⁻⁴	
Small – Signal Current Gain (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kH	h _{fe}	75	375	_	
Output Admittance (V _{CE} = 10 Vdc, I _C = 10 mAdc, f = 1.0 kH	h _{oe}	25	200	μmhos	
Noise Figure (V _{CE} = 10 Vdc, I _C = 100 μAdc, R _S = 1.0	NF	-	4.0	dB	
SWITCHING CHARACTERISTICS		· ·		·	-
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = -0.5 Vdc,	t _d	-	10	
Rise Time	$I_{\rm C} = 150 \text{ mAdc}, I_{\rm B1} = 15 \text{ mAdc})$	t _r	-	25	ns
Storage Time	(V _{CC} = 30 Vdc, I _C = 150 mAdc,	t _s	-	225	
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$	t _f	-	60	ns

1. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

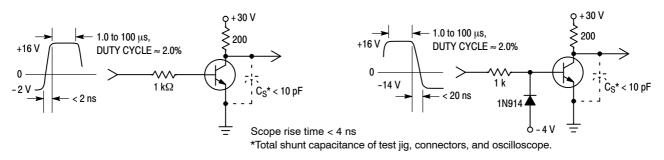
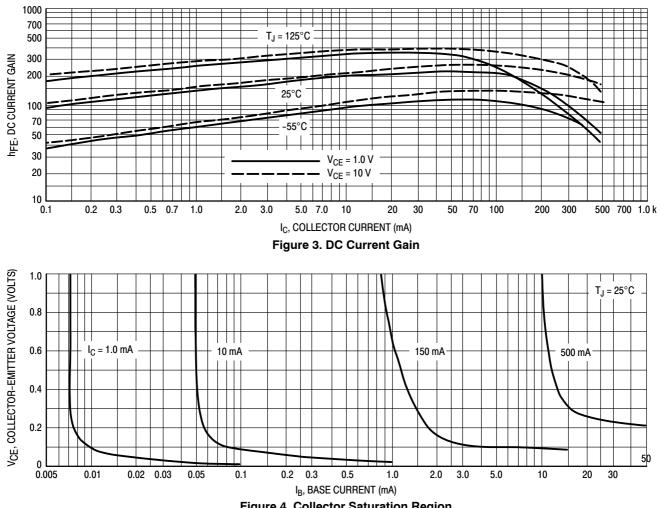




Figure 2. Turn-Off Time





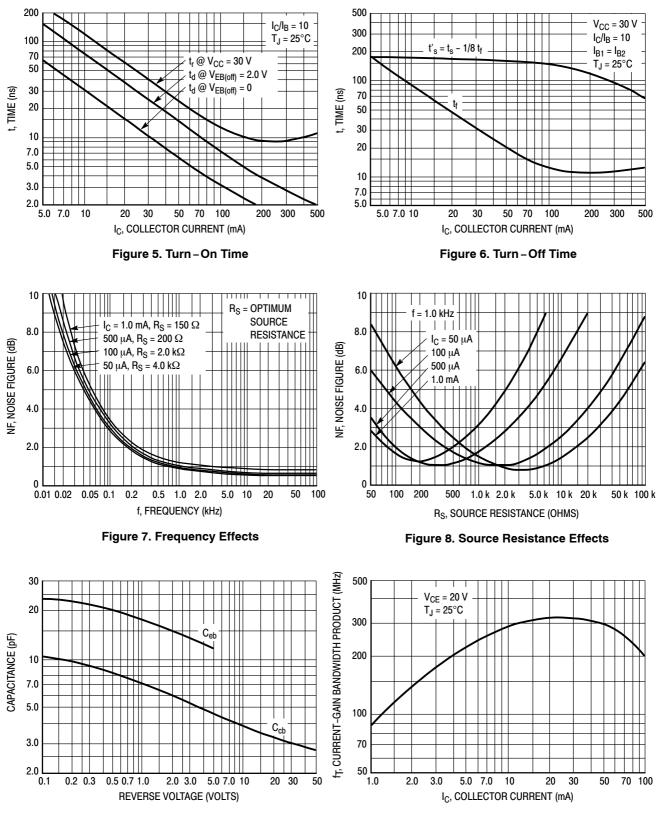
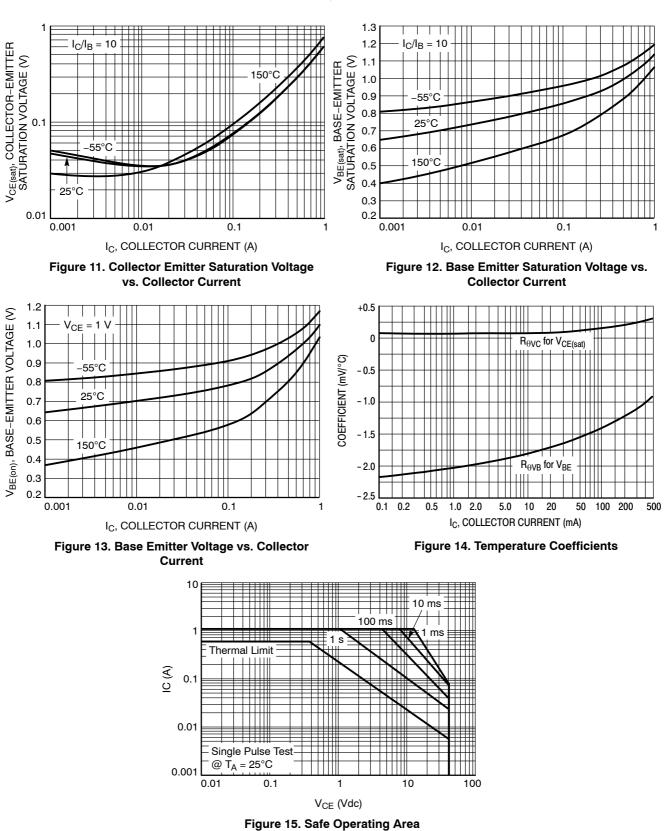


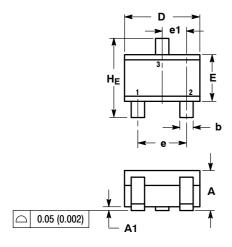
Figure 9. Capacitances

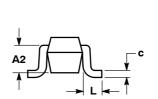
Figure 10. Current–Gain Bandwidth Product



PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 ISSUE N





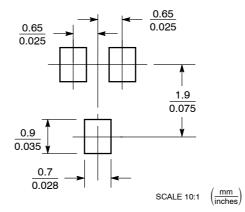
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
с	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
Е	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BSC	;
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095



SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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